AMENDMENTS TO THE SPECIFICATION

In the clean substitute specification filed on July 11, 2007, please replace the paragraph beginning at page 13, line 26, with the following rewritten paragraph.

-- Then, the oxide film for preventing contamination is removed using a chemical agent, such as hydrofluoric acid, and then another oxide film of about 100 nm is formed, and subjected to heat treatment in a nitrogen gas atmosphere at 800 °C for about 10 minutes, and subjected to RTA (rapid thermal anneal) in a nitrogen gas atmosphere at 1,000 °C for about 10 seconds, so that As in the polycrystalline silicon 6 undergoes thermal diffusion from the emitter electrode lead portion 40, thus forming an emitter region 41 in the base layer 18. Then, the oxide film of 100 nm formed before the heat treatment is removed using a chemical agent, such as hydrofluoric acid. --